

**INFORMATION DISCLOSURE STATEMENT**

Applicant	:	Arthur Sherman
App. No.	:	Unknown
Filed	:	Herewith
For	:	SEQUENTIAL CHEMICAL VAPOR DEPOSITION
Examiner	:	Unknown
Group Art Unit	:	Unknown

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing two hundred forty-three (243) references that were previously disclosed to or cited by the Patent and Trademark Office in the prosecution of U.S. patent application No. 09/866,156, filed May 24, 2001, which is the parent of this application, and is relied upon for an earlier filing date under 35 U.S.C. § 120. Copies of the references are not submitted pursuant to 37 C.F.R. § 1.98(d). This Information Disclosure Statement is being filed with an RCE or within three months of the filing date of this application and no fee is required in accordance with 37 C.F.R. § 1.97(b)(1), (b)(2), or (b)(4).

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: October 22, 2003

By: 

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Attorney of Record  
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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  <b>INFORMATION DISCLOSURE STATEMENT          BY APPLICANT</b>  (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. ASMMC.9CP1DV1D	APPLICATION NO. To be assigned
	APPLICANT Arthur Sherman	
	FILING DATE Concurrently herewith	GROUP Unknown

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1.	4,058,430	11/15/77	Suntola et al.	156	611	11/25/75
	2.	4,282,267	08/04/81	Küyel			
	3.	4,389,973	06/28/83	Suntola et al.	118	725	12/11/81
	4.	4,747,367	05/31/88	Posa			
	5.	4,761,269	08/02/88	Conger et al.			
	6.	4,767,494	08/30/88	Kobayashi	156	606	09/19/86
	7.	4,845,049	07/04/89	Sunakawa	437	81	03/28/88
	8.	4,851,095	07/89	Scobey et al.			
	9.	4,859,627	08/22/89	Sunakawa	437	81	07/01/88
	10.	4,876,218	10/24/89	Pessa et al.	437	107	09/26/88
	11.	4,935,661	06/90	Heinecke et al.			
	12.	4,935,661-A	06/1990	Heinecke et al.			
	13.	4,993,357	02/19/91	Scholz	118	715	12/21/89
	14.	5,060,595	10/29/91	Ziv et al.	118	722	
	15.	5,071,670	12/10/91	Kelly	427	38	
	16.	5,130,269	07/14/92	Kitahara et al.	437	111	04/25/89
	17.	5,166,092	11/24/92	Mochizuki et al.	437	105	10/30/90
	18.	5,225,366	07/06/93	Yoder	437	108	07/22/90
	19.	5,256,244	10/26/93	Ackerman	156	613	02/10/92
	20.	5,270,247	12/14/93	Sakuma et al.	437	133	07/08/92
	21.	5,278,435	01/11/94	Van Hove			
	22.	5,281,274	01/25/94	Yoder			
	23.	5,291,066	03/01/94	Neugebauer			
	24.	5,294,286	03/15/94	Neugebauer			
	25.	5,300,186	04/05/94	Kitahara			
	26.	5,306,666	04/26/94	Izumi	437	192	07/21/93
	27.	5,321,713	06/14/94	Khan			

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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
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	29.	5,356,673	10/94	Schmitt et al.			
	30.	5,374,570	12/20/94	Nasu			
	31.	5,395,791	03/07/95	Cheng			
	32.	5,443,033	08/22/95	Nishizawa			
	33.	5,443,647	08/22/95	Aucoin et al.			
	34.	5,458,084	10/17/95	Thorne			
	35.	5,469,806	11/28/95	Mochizuki			
	36.	5,483,919	01/16/96	Kitahara			
	37.	5,484,664	01/16/96	Yokoyama			
	38.	5,496,582	03/05/96	Mizutani			
	39.	5,618,395	04/08/97	Gartner			
	40.	5,641,984	06/24/97	Aftergut			
	41.	5,693,139	12/02/97	Nishizawa et al.	117	89	06/15/93
	42.	5,707,880	01/13/98	Aftergut			
	43.	5,711,811	01/27/98	Suntola			
	44.	5,730,802	03/24/98	Ishizumi			
	45.	5,769,950	06/23/98	Takasu et al.			
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	47.	5,916,365	06/99	Sherman			
	48.	5,916,365	06/1999	Sherman			
	49.	6,200,893	03/13/01	Sneh			
	50.	6,203,613	03/20/01	Gates et al.	117	104	10/19/99
	51.	6,270,572	08/07/01	Kim et al.	117	93	08/09/99
	52.	6,342,277	01/2002	Sherman			
	53.	US 2001/0028922	10/2001	Sandhu, Gurtej S.	427	255.27	

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FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	54.	WO 00/63957	26.10 00	PCT	H01L21	205		
	55.	0 442 490 A1	21.08 91	Europe				
	56.	0 526 779 A1	10.02 93	Europe				
	57.	1 167 567 A1	02.01 02	Europe				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)							
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EXAMINE R INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
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